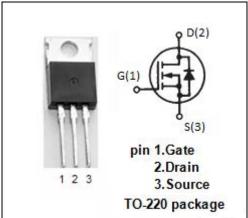


isc N-Channel MOSFET Transistor

PSMN2R7-30PL

FEATURES

- Drain Current –I_D= 100A@ T_C=25 °C
- · Drain Source Voltage-
 - : V_{DSS}= 30V(Min)
- · Static Drain-Source On-Resistance
- : $R_{DS(on)} = 2.7m \Omega (Max)$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



DESCRIPTION

 Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage-Continuous	±20	V
I _D	Drain Current-Continuous	100	А
I _{DM}	Drain Current-Single Pluse	730	А
P _D	Total Dissipation @T _C =25℃	170	W
TJ	Max. Operating Junction Temperature	-55~175	$^{\circ}$
T _{stg}	Storage Temperature	-55~175	$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.88	°C/W

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¢ †		;	m MAX	R
; ; ;	DIM	m MIN	MAX 15.90	R
c	DIM A	m MIN 15.50	MAX 15.90	R
c	DIM A B	MIN 15.50 9.80	MAX 15.90 10.20	R -
c	DIM A B C	MIN 15.50 9.80	MAX 15.90 10.20	R -
c	DIM A B C	m MIN 15.50 9.80 4.20	MAX 15.90 10.20 4.50 0.90	R -
c	DIM A B C D	MIN 15.50 9.80 4.20 0.70 3.40	MAX 15.90 10.20 4.50 0.90 3.70	R
c	DIM A B C D F	m MIN 15.50 9.80 4.20 0.70 3.40 4.98	MAX 15.90 10.20 4.50 0.90 3.70	R
c	DIM A B C D	MIN 15.50 9.80 4.20 0.70 3.40	MAX 15.90 10.20 4.50 0.90	R

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6.45

1.45

1.35 6.65

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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	30		V
V _{GS(th)}	Gate Threshold Voltage	V_{DS} = V_{GS} ; I_D = 1mA	1.3	2.15	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 15A		2.7	mΩ
Igss	Gate-Body Leakage Current	V _{GS} = ±16V;V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 30V; V _{GS} = 0		5.0	μА
V _{SD}	Forward On-Voltage	I _S = 15A; V _{GS} = 0		1.2	V

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